

NJ72 Process

Silicon Junction Field-Effect Transistor

• VHF/UHF Amplifier

Absolute maximum ratings at TA = 25 °C

Gate Current, I _G	10 mA
Operating Junction Temperature, T _j	+150°C
Storage Temperature, T _s	– 65°C to +175°C

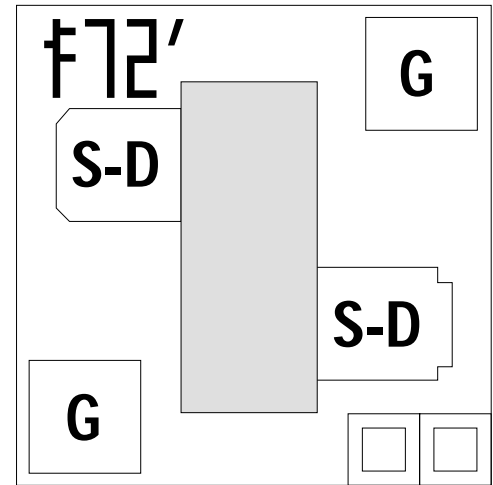
Devices in this Databook based on the NJ72 Process.

Datasheet

IFN5564, IFN5565
IFN5566
J308, J309
J308, J309
J310

Datasheet

U308, U309
U430, U431
VCR2N



Die Size = 0.020" X 0.020"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

At 25°C free air temperature:

Static Electrical Characteristics

		NJ72 Process					
		Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	V _{(BR)GSS}	– 25	– 40		V	I _G = – 1 μA, V _{DS} = 0V	
Reverse Gate Leakage Current	I _{GSS}		– 10	– 100	pA	V _{GS} = – 15V, V _{DS} = 0V	
Drain Saturation Current (Pulsed)	I _{DSS}	5		90	mA	V _{DS} = 15V, V _{GS} = 0V	
Gate Source Cutoff Voltage	V _{GS(OFF)}	– 1		– 5.5	V	V _{DS} = 15V, I _D = 1 nA	

Dynamic Electrical Characteristics

Forward Transconductance	g _{fs}		22		mS	V _{DS} = 15V, V _{GS} = 0V	f = 1 kHz
Drain Source ON Resistance	r _{ds(on)}		40		Ω	I _D = 1 mA, V _{GS} = 0V	f = 1 kHz
Input Capacitance	C _{iss}		6.5		pF	V _{DS} = 0V, V _{GS} = – 10V	f = 1 MHz
Feedback Capacitance	C _{rss}		2.5		pF	V _{DS} = 0V, V _{GS} = – 10V	f = 1 MHz



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